

CD74HC14, CD74HCT14

High Speed CMOS Logic Hex Inverting Schmitt Trigger

Features

- Unlimited Input Rise and Fall Times
- Exceptionally High Noise Immunity
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC}

at $V_{CC} = 5V$

- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

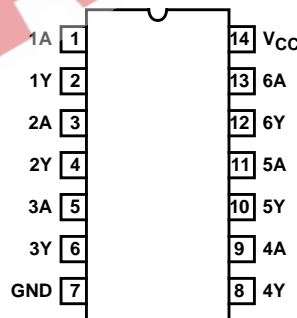
The Harris CD74HC14, CD74HCT14 each contain 6 inverting Schmitt Triggers in one package.

Ordering Information

| PART NUMBER | TEMP. RANGE (°C) | PACKAGE | PKG. NO. |
|-------------|------------------|--------------|----------|
| CD54HCT14E | -55 to 125 | 14 Ld CERDIP | F14.3 |

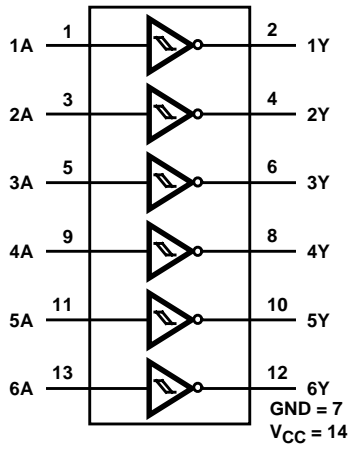
Pinout

CD54HC14, CD54HCT14, CD74HC14, CD74HCT14
(PDIP, CERDIP, SOIC)
TOP VIEW



CD74HC14, CD74HCT14

Functional Diagram

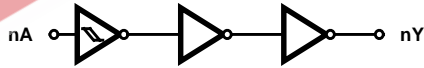


TRUTH TABLE

| INPUT (A) | OUTPUT (Y) |
|-----------|------------|
| L | H |
| H | L |

NOTE:
H= High Level
L = Low Level

Logic Diagram



CD74HC14, CD74HCT14

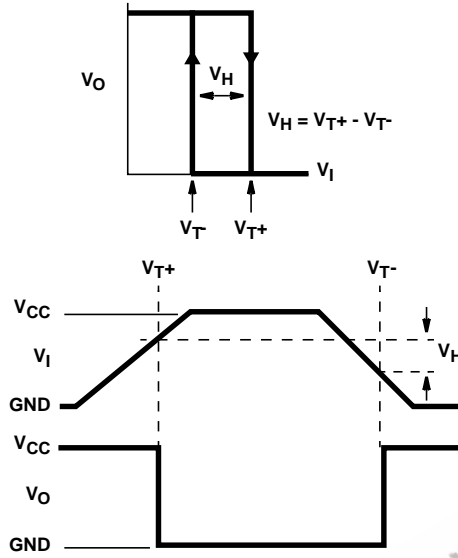


FIGURE 3. HYSTERESIS DEFINITION, CHARACTERISTIC, AND TEST SETUP

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CD74HC14, CD74HCT14

Absolute Maximum Ratings

| | |
|--|-------------|
| DC Supply Voltage, V_{CC} | -0.5V to 7V |
| DC Input Diode Current, I_{IK} | |
| For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$ | $\pm 20mA$ |
| DC Output Diode Current, I_{OK} | |
| For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$ | $\pm 20mA$ |
| DC Drain Current, per Output, I_O | |
| For $-0.5V < V_O < V_{CC} + 0.5V$ | $\pm 25mA$ |
| DC Output Source or Sink Current per Output Pin, I_O | |
| For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$ | $\pm 25mA$ |
| DC V_{CC} or Ground Current, I_{CC} | $\pm 50mA$ |

Thermal Information

| | | |
|--|------------------------------------|---------------------------------|
| Thermal Resistance (Typical, Note 3) | θ_{JA} ($^{\circ}C/W$) | θ_{JC} ($^{\circ}C/W$) |
| PDIP Package | 90 | - |
| CERDIP Package | 130 | 55 |
| SOIC Package | 120 | - |
| Maximum Junction Temperature (Hermetic Package or Die) ... | 175 $^{\circ}C$ | |
| Maximum Junction Temperature (Plastic Package) | 150 $^{\circ}C$ | |
| Maximum Storage Temperature Range | -65 $^{\circ}C$ to 150 $^{\circ}C$ | |
| Maximum Lead Temperature (Soldering 10s) | 300 $^{\circ}C$ | |
| | (SOIC - Lead Tips Only) | |

Operating Conditions

| | |
|---|------------------------------------|
| Temperature Range, T_A | -55 $^{\circ}C$ to 125 $^{\circ}C$ |
| Supply Voltage Range, V_{CC} | |
| HC Types | 2V to 6V |
| HCT Types | 4.5V to 5.5V |
| DC Input or Output Voltage, V_I , V_O | 0V to V_{CC} |
| Input Rise and Fall Time, t_r , t_f | |
| 2V | 100ms (Max) |
| 4.5V | 100ms (Max) |
| 6V | 100ms (Max) |

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

| PARAMETER | SYMBOL | TEST CONDITIONS | | | 25 $^{\circ}C$ | | -40 $^{\circ}C$ TO 85 $^{\circ}C$ | | -55 $^{\circ}C$ TO 125 $^{\circ}C$ | | UNITS | |
|--------------------------------------|----------|----------------------|------------|--------------|----------------|------|-----------------------------------|------|------------------------------------|------|-------|---|
| | | V_I (V) | I_O (mA) | V_{CC} (V) | MIN | MAX | MIN | MAX | MIN | MAX | | |
| HC TYPES | | | | | | | | | | | | |
| Input Switch Points | V_{T+} | - | - | 2 | 0.7 | 1.5 | 0.7 | 1.5 | 0.7 | 1.5 | V | |
| | | | | 4.5 | 1.7 | 3.15 | 1.7 | 3.15 | 1.7 | 3.15 | V | |
| | | | | 6 | 2.1 | 4.2 | 2.1 | 4.2 | 2.1 | 4.2 | V | |
| | V_{T-} | - | - | 2 | 0.3 | 1.0 | 0.3 | 1.0 | 0.3 | 1.0 | V | |
| | | | | 4.5 | 0.9 | 2.2 | 0.9 | 2.2 | 0.9 | 2.2 | V | |
| | | | | 6 | 1.2 | 3.0 | 1.2 | 3.0 | 1.2 | 3.0 | V | |
| | V_H | - | - | 2 | 0.2 | 1.0 | 0.2 | 1.0 | 0.2 | 1.0 | V | |
| | | | | 4.5 | 0.4 | 1.4 | 0.4 | 1.4 | 0.4 | 1.4 | V | |
| | | | | 6 | 0.6 | 1.6 | 0.6 | 1.6 | 0.6 | 1.6 | V | |
| High Level Output Voltage CMOS Loads | V_{OH} | V_{T-} or V_{T+} | -0.02 | -0.02 | 2 | 1.9 | - | 1.9 | - | 1.9 | - | V |
| | | | -0.02 | -0.02 | 4.5 | 4.4 | - | 4.4 | - | 4.4 | - | V |
| | | | -0.02 | -0.02 | 6 | 5.9 | - | 5.9 | - | 5.9 | - | V |
| High Level Output Voltage TTL Loads | V_{OH} | V_{T-} or V_{T+} | - | - | - | - | - | - | - | - | - | V |
| | | | -4 | -4 | 4.5 | 3.98 | - | 3.84 | - | 3.7 | - | V |
| | | | -5.2 | -5.2 | 6 | 5.48 | - | 5.34 | - | 5.2 | - | V |

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DC Electrical Specifications (Continued)

| PARAMETER | SYMBOL | TEST CONDITIONS | | V_{CC} (V) | 25°C | | -40°C TO 85°C | | -55°C TO 125°C | | UNITS |
|--|-----------------------------|-------------------------|------------|---------------|------|-----------|---------------|---------|----------------|---------|---------|
| | | V_I (V) | I_O (mA) | | MIN | MAX | MIN | MAX | MIN | MAX | |
| Low Level Output Voltage CMOS Loads | V_{OL} | V_{IH} or V_{IL} | 0.02 | 2 | - | 0.1 | - | 0.1 | - | 0.1 | V |
| | | | 0.02 | 4.5 | - | 0.1 | - | 0.1 | - | 0.1 | V |
| | | | 0.02 | 6 | - | 0.1 | - | 0.1 | - | 0.1 | V |
| Low Level Output Voltage TTL Loads | V_{OL} | V_{IH} or V_{IL} | - | - | - | - | - | - | - | - | V |
| | | | 4 | 4.5 | - | 0.26 | - | 0.33 | - | 0.4 | V |
| | | | 5.2 | 6 | - | 0.26 | - | 0.33 | - | 0.4 | V |
| Input Leakage Current | I_I | V_{CC} or GND | - | 6 | - | ± 0.1 | - | ± 1 | - | ± 1 | μA |
| Quiescent Device Current | I_{CC} | V_{CC} or GND | 0 | 6 | - | 2 | - | 20 | - | 40 | μA |
| HCT TYPES | | | | | | | | | | | |
| Input Switch Points | V_{T+} | - | - | 4.5 | 1.2 | 1.9 | 1.2 | 1.9 | 1.2 | 1.9 | V |
| | | | | 5.5 | 1.4 | 2.1 | 1.4 | 2.1 | 1.4 | 2.1 | V |
| | V_{T-} | | | 4.5 | 0.5 | 1.2 | 0.5 | 1.2 | 0.5 | 1.2 | V |
| | | | | 5.5 | 0.6 | 1.4 | 0.6 | 1.4 | 0.6 | 1.4 | V |
| | V_H | | | 4.5 | 0.4 | 1.4 | 0.4 | 1.4 | 0.4 | 1.4 | V |
| 5.5 | 0.4 | 1.5 | 0.4 | 1.5 | 0.4 | 1.5 | V | | | | |
| High Level Output Voltage CMOS Loads | V_{OH} | V_{IH} or V_{IL} | -0.02 | 4.5 | 4.4 | - | 4.4 | - | 4.4 | - | V |
| High Level Output Voltage TTL Loads | | | -4 | 4.5 | 3.98 | - | 3.84 | - | 3.7 | - | V |
| Low Level Output Voltage CMOS Loads | V_{OL} | V_{IH} or V_{IL} | 0.02 | 4.5 | - | 0.1 | - | 0.1 | - | 0.1 | V |
| Low Level Output Voltage TTL Loads | | | 4 | 4.5 | - | 0.26 | - | 0.33 | - | 0.4 | V |
| Input Leakage Current | I_I | V_{CC} and GND | - | 5.5 | - | ± 0.1 | - | ± 1 | - | ± 1 | μA |
| Quiescent Device Current | I_{CC} | V_{CC} or GND | 0 | 5.5 | - | 2 | - | 20 | - | 40 | μA |
| Additional Quiescent Device Current Per Input Pin: 1 Unit Load | ΔI_{CC} (Note 4) | V_{CC} - 2.1 | - | 4.5 to 5.5 | - | 360 | - | 450 | - | 490 | μA |

NOTE:

4. For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

HCT Input Loading Table

| INPUT | UNIT LOADS |
|-------|------------|
| nA | 0.6 |

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360 μA max at 25°C.

Switching Specifications Input $t_r, t_f = 6\text{ns}$

| PARAMETER | SYMBOL | TEST CONDITIONS | V_{CC} (V) | 25°C | | | -40°C TO 85°C | | -55°C TO 125°C | | UNITS |
|--|--------------------|---------------------|--------------|------|-----|-----|---------------|-----|----------------|-----|-------|
| | | | | MIN | TYP | MAX | MIN | MAX | MIN | MAX | |
| HC TYPES | | | | | | | | | | | |
| Propagation Delay, A to Y | t_{PLH}, t_{PHL} | $C_L = 50\text{pF}$ | 2 | - | - | 135 | - | 170 | - | 205 | ns |
| | | $C_L = 50\text{pF}$ | 4.5 | - | - | 27 | - | 34 | - | 41 | ns |
| | | $C_L = 15\text{pF}$ | 5 | - | 11 | - | - | - | - | - | ns |
| | | $C_L = 50\text{pF}$ | 6 | - | - | 23 | - | 29 | - | 35 | ns |
| Output Transition Times | t_{TLH}, t_{THL} | $C_L = 50\text{pF}$ | 2 | - | - | 75 | - | 95 | 18 | 110 | ns |
| | | | 4.5 | - | - | 15 | - | 19 | - | 22 | ns |
| | | | 6 | - | - | 13 | - | 16 | - | 19 | ns |
| Input Capacitance | C_I | - | - | - | 10 | - | 10 | - | 10 | pF | |
| Power Dissipation Capacitance (Notes 5, 6) | C_{PD} | - | 5 | - | 20 | - | - | - | - | pF | |
| HCT TYPES | | | | | | | | | | | |
| Propagation Delay, A to Y | t_{PLH}, t_{PHL} | $C_L = 50\text{pF}$ | 4.5 | - | - | 38 | - | 48 | - | 57 | ns |
| | | $C_L = 15\text{pF}$ | 5 | - | 16 | - | - | - | - | - | ns |
| Output Transition Times | t_{TLH}, t_{THL} | $C_L = 50\text{pF}$ | 4.5 | - | - | 15 | - | 19 | - | 22 | ns |
| Input Capacitance | C_I | - | - | - | 10 | - | 10 | - | 10 | pF | |
| Power Dissipation Capacitance (Notes 5, 6) | C_{PD} | - | 5 | - | 20 | - | - | - | - | pF | |

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per inverter.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency, C_L = output load capacitance, V_{CC} = supply voltage.

Test Circuits and Waveforms

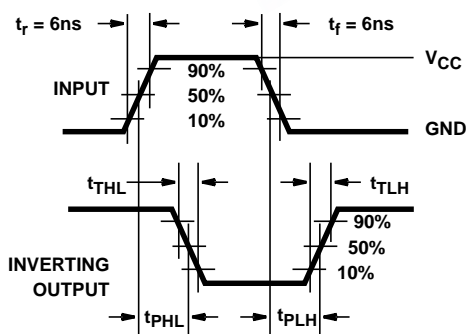


FIGURE 4. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

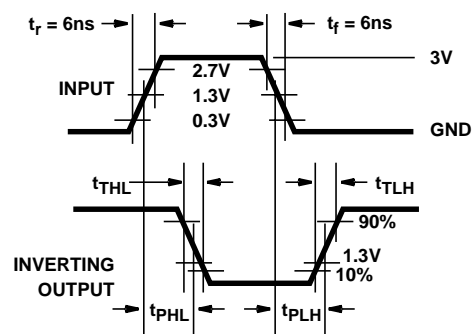


FIGURE 5. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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